

# LM4030 SOT-23 Ultra-High Precision Shunt Voltage Reference

Check for Samples: LM4030

## FEATURES

- High Output Voltage Accuracy 0.05%
- Low Temperature Coefficient 10 ppm/°C
- Extended Temperature Operation -40-125°C
- Excellent Thermal Hysteresis, 75ppm
- Excellent Long-Term Stability, 40ppm
- High Immunity to Board Stress Effects
- Capable of Handling 50 mA Transients
- Voltage Options 2.5V, 4.096V
- SOT-23 Package

### **APPLICATIONS**

- Data Acquisition/Signal path
- Test and Measurement
- Automotive & Industrial
- Communications
- Instrumentation
- Power Management

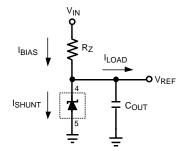
## **Typical Application Circuit**

## DESCRIPTION

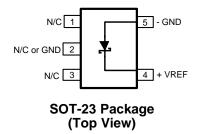
The LM4030 is an ultra-high precision shunt voltage reference, having exceptionally high initial accuracy (0.05%) and temperature stability (10ppm/°C). The LM4030 is available with fixed voltage options of 2.5V and 4.096V. Despite the tiny SOT-23 package, the LM4030 exhibits excellent thermal hysteresis (75ppm) and long-term stability (40ppm) as well as immunity to board stress effects.

The LM4030 is designed to operate without an external capacitor, but any capacitor up to  $10\mu$ F may be used. The LM4030 can be powered off as little as  $120\mu$ A (max) but is capable of shunting up to 30mA continuously. As with any shunt reference, the LM4030 can be powered off of virtually any supply and is a simple way to generate a highly accurate system reference.

The LM4030 is available in three grades (A, B, and C). The best grade devices (A) have an initial accuracy of 0.05% with ensured temperature coefficient of 10 ppm/°C or less, while the lowest grade parts (C) have an initial accuracy of 0.15% and a temperature coefficient of 30 ppm/°C.



## **Connection Diagram**



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. All trademarks are the property of their respective owners.

#### SNVS552B - MARCH 2008 - REVISED APRIL 2013

www.ti.com

#### **PIN DESCRIPTIONS**

Pin #	Name	Function
1	N/C	No connect pin, leave floating
2	GND, N/C	Ground or no connect
3	N/C	No connect pin, leave floating
4	VREF	Reference voltsge
5	GND	Ground



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### Absolute Maximum Ratings (1)(2)

Maximum Voltage on any input	-0.3 to 6V
Power Dissipation ( $T_A = 25^{\circ}C$ ) <sup>(3)</sup>	350mW
Storage Temperature Range	−65°C to 150°C
Lead Temperature (soldering, 10sec)	260°C
Vapor Phase (60 sec)	215°C
Infrared (15sec)	220°C
ESD Susceptibility <sup>(4)</sup> Human Body Model	2kV

Absolute Maximum Ratings indicate limits beyond which damage may occur to the device. Operating Ratings indicate conditions for (1) which the device is intended to be functional, but do not ensure specific performance limits. For ensured specifications, see Electrical Characteristics.

If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and (2) specifications.

Without PCB copper enhancements. The maximum power dissipation must be de-rated at elevated temperatures and is limited by TJMAX (3) (maximum junction temperature), θ<sub>J-A</sub> (junction to ambient thermal resistance) and T<sub>A</sub> (ambient temperature). The maximum power dissipation at any temperature is:  $P_{\text{DissMAX}} = (T_{\text{JMAX}} - T_{\text{A}})/\theta_{\text{J-A}}$  up to the value listed in the Absolute Maximum Ratings.  $\theta_{\text{J-A}}$  for SOT-23 package is 220°C/W,  $T_{\text{JMAX}} = 125^{\circ}$ C. The human body model is a 100 pF capacitor discharged through a 1.5 k $\Omega$  resistor into each pin.

(4)

#### **Operating Ratings**

Maximum Continuous Shunt Current	30mA
Maximum Shunt Current (<1s)	50mA
Junction Temperature Range (T <sub>J</sub> )	-40°C to +125°C

#### Electrical Characteristics LM4030-2.5 (V<sub>OUT</sub> = 2.5V)

Limits in standard type are for  $T_J = 25^{\circ}$ C only, and limits in boldface type apply over the junction temperature ( $T_J$ ) range of -40°C to +125°C. Minimum and Maximum limits are ensured through test, design, or statistical correlation. Typical values represent the most likely parametric norm at  $T_J = 25^{\circ}$ C, and are provided for reference purposes only.

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур <sup>(2)</sup>	Max <sup>(1)</sup>	Unit
V <sub>REF</sub>	Reverse Breakdown Voltage	I <sub>SHUNT</sub> = 120µA		2.5		V
	Reverse Breakdown Voltage Tolerance	e (I <sub>SHUNT</sub> = 120µA)				
	LM4030A-2.5	(A Grade - 0.05%)	-0.05		0.05	%
	LM4030B-2.5	(B Grade - 0.10%)	-0.10		0.10	%
	LM4030C-2.5	(C Grade - 0.15%)	-0.15		0.15	%
I <sub>RMIN</sub>	Minimum Operating Current				120	μA
TC	Temperature Coefficient (3)					
	LM4030A-2.5	0°C ≤ T <sub>J</sub> ≤ + 85°C			10	ppm / °C
		-40°C ≤ T <sub>J</sub> ≤ +125°C			20	ppm / °C
	LM4030B-2.5	-40°C ≤ T <sub>J</sub> ≤ +125°C			20	ppm / °C
	LM4030C-2.5	-40°C ≤ T <sub>J</sub> ≤ +125°C			30	ppm / °C
$\Delta V_{REF} / \Delta I_{SHUNT}$	Reverse Breakdown Voltage Change with Current	160µA ≤ I <sub>SHUNT</sub> ≤ 30mA		25	110	ppm / mA
$\Delta V_{REF}$	Long Term Stability <sup>(4)</sup>	1000 Hrs, T <sub>A</sub> = 30°C		40		ppm
V <sub>HYST</sub>	Thermal Hysteresis <sup>(5)</sup>	-40°C ≤ T <sub>J</sub> ≤ +125°C		75		ppm
V <sub>N</sub>	Output Noise Voltage (6)	0.1 Hz to 10 Hz		105		μV <sub>PP</sub>

(1) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlation using Statistical Quality Control.

(2) Typical numbers are at 25°C and represent the most likely parametric norm.

(3) Temperature coefficient is measured by the "Box" method; i.e., the maximum  $\Delta V_{REF}$  is divided by the maximum  $\Delta T$ .

(4) Long term stability is  $V_{REF} @25^{\circ}C$  measured during 1000 hrs. This measurement is taken for  $I_{R} = 500 \ \mu$ A.

(5) Thermal hysteresis is defined as the change in +25°C output voltage before and after cycling the device from (-40°C to 125°C) eight times.

(6) Low frequency peak-to-peak noise measured using first-order 0.1 Hz HPF and second-order 10 Hz LPF.

### Electrical Characteristics LM4030-4.096 (V<sub>OUT</sub> = 4.096V)

Limits in standard type are for  $T_J = 25^{\circ}$ C only, and limits in boldface type apply over the junction temperature ( $T_J$ ) range of -40°C to +125°C. Minimum and Maximum limits are ensured through test, design, or statistical correlation. Typical values represent the most likely parametric norm at  $T_J = 25^{\circ}$ C, and are provided for reference purposes only.

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур <sup>(2)</sup>	Max <sup>(1)</sup>	Unit
V <sub>REF</sub>	Reverse Breakdown Voltage	I <sub>SHUNT</sub> = 130μA		4.096		V
	Reverse Breakdown Voltage Tolerance	( Ι <sub>SHUNT</sub> = 130μΑ)				
	LM4030A-4.096	(A Grade - 0.05%)	-0.05		0.05	%
	LM4030B-4.096	(B Grade - 0.10%)	-0.10		0.10	%
	LM4030C-4.096	(C Grade - 0.15%)	-0.15		0.15	%
I <sub>RMIN</sub>	Minimum Operating Current				130	μA
TC	Temperature Coefficient (3)					
	LM4030A-4.096	0°C ≤ T <sub>J</sub> ≤ + 85°C			10	ppm / °C
		-40°C ≤ T <sub>J</sub> ≤ +125°C			20	ppm / °C
	LM4030B-4.096	-40°C ≤ T <sub>J</sub> ≤ +125°C			20	ppm / °C
	LM4030C-4.096	-40°C ≤ T <sub>J</sub> ≤ +125°C			30	ppm / °C
ΔV <sub>REF</sub> /ΔI <sub>LOAD</sub>	Reverse Breakdown Voltage Change with Current	$160\mu A \le I_{SHUNT} \le 30mA$		15	95	ppm / m/

(1) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlation using Statistical Quality Control.

(2) Typical numbers are at 25°C and represent the most likely parametric norm.

(3) Temperature coefficient is measured by the "Box" method; i.e., the maximum  $\Delta V_{REF}$  is divided by the maximum  $\Delta T$ .

Copyright © 2008–2013, Texas Instruments Incorporated



## Electrical Characteristics LM4030-4.096 (V<sub>OUT</sub> = 4.096V) (continued)

Limits in standard type are for  $T_J = 25^{\circ}$ C only, and limits in boldface type apply over the junction temperature ( $T_J$ ) range of -40°C to +125°C. Minimum and Maximum limits are ensured through test, design, or statistical correlation. Typical values represent the most likely parametric norm at  $T_J = 25^{\circ}$ C, and are provided for reference purposes only.

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Typ <sup>(2)</sup>	Max <sup>(1)</sup>	Unit
$\Delta V_{REF}$	Long Term Stability <sup>(4)</sup>	1000 Hrs, T <sub>A</sub> = 30°C		40		ppm
V <sub>HYST</sub>	Thermal Hysteresis (5)	$-40^{\circ}C \le T_{J} \le +125^{\circ}C$		75		ppm
V <sub>N</sub>	Output Noise Voltage (6)	0.1 Hz to 10 Hz		165		μV <sub>PP</sub>

(4) Long term stability is  $V_{REF}$  @25°C measured during 1000 hrs. This measurement is taken for  $I_R = 500 \ \mu$ A.

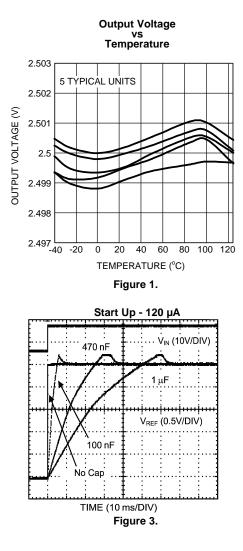
(5) Thermal hysteresis is defined as the change in +25°C output voltage before and after cycling the device from (-40°C to 125°C) eight times.

(6) Low frequency peak-to-peak noise measured using first-order 0.1 Hz HPF and second-order 10 Hz LPF.

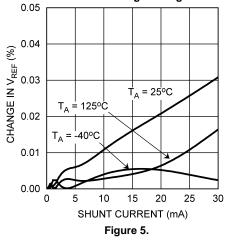


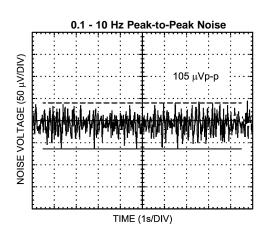
SNVS552B - MARCH 2008 - REVISED APRIL 2013



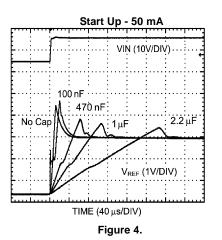






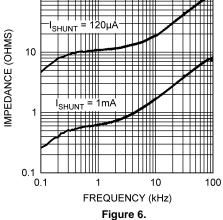






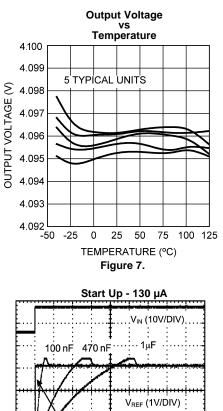


100

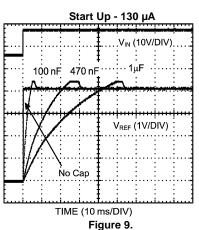


#### SNVS552B - MARCH 2008 - REVISED APRIL 2013

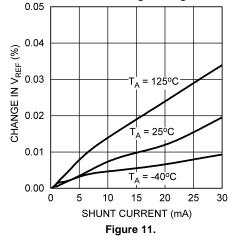
www.ti.com







**Reverse Breakdown Voltage Change with Current** 



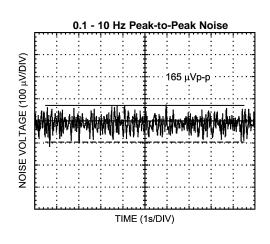
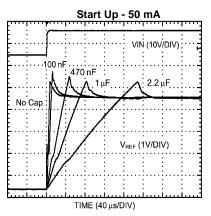
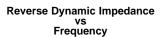
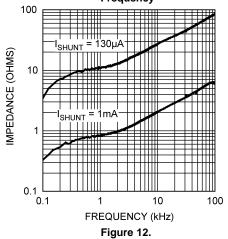


Figure 8.





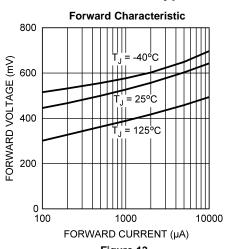


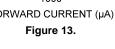




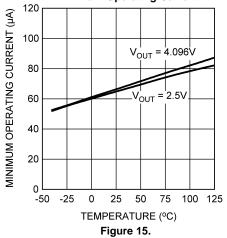
#### SNVS552B - MARCH 2008 - REVISED APRIL 2013

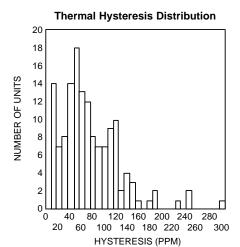




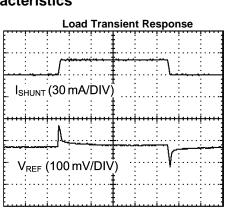






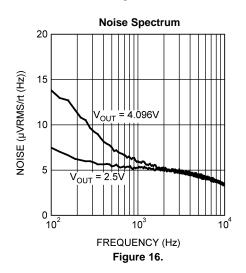


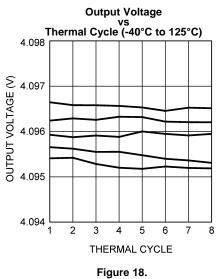




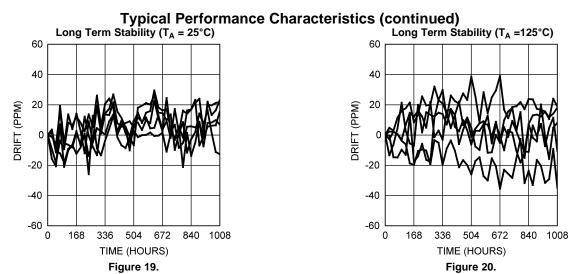
TIME (10 µs/DIV)

Figure 14.





#### SNVS552B-MARCH 2008-REVISED APRIL 2013





(1)

#### **APPLICATION INFORMATION**

#### THEORY OF OPERATION

The LM4030 is an ultra-high precision shunt voltage reference, having exceptionally high initial accuracy (0.05%) and temperature stability (10ppm/°C). The LM4030 is available with fixed voltage options of 2.5V and 4.096V. Despite the tiny SOT-23 package, the LM4030 exhibits excellent thermal hysteresis (75ppm) and long-term stability (25ppm). The LM4030 is designed to operate without an external capacitor, but any capacitor up to 10  $\mu$ F may be used. The LM4030 can be powered off as little as 120  $\mu$ A (max) but is capable of shunting up to 30 mA continuously. The typical application circuit for the LM4030 is shown in Figure 21.

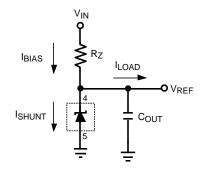


Figure 21. Typical Application Circuit

#### **COMPONENT SELECTION**

A resistor must be chosen to set the maximum operating current for the LM4030 ( $R_z$  in Figure 21). The value of the resistor can be calculated using the following equation:

 $R_{Z} = (V_{IN} - V_{REF})/(I_{MIN_OPERATING} + I_{LOAD_MAX})$ 

 $R_Z$  is chosen such that the total current flowing through  $R_Z$  is greater than the maximum load current plus the minimum operating current of the reference itself. This ensures that the reference is never starved for current. Running the LM4030 at higher currents is advantageous for reducing noise. The reverse dynamic impedance of the V<sub>REF</sub> node scales inversely with the shunted current (see Figure 22) leading to higher rejection of noise emanating from the input supply and from EMI (electro-magnetic interference).

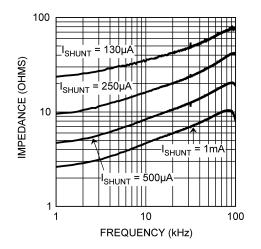


Figure 22. Reverse Dynamic Impedance vs IOUT

The LM4030 is designed to operate with or without a bypass capacitor ( $C_{OUT}$  in Figure 21) and is stable with capacitors of up to 10  $\mu$ F. The use of a bypass capacitor can improve transient response and reduce broadband noise. Additionally, a bypass capacitor will counter the rising reverse dynamic impedance at higher frequencies improving noise immunity (see Figure 23).

Copyright © 2008–2013, Texas Instruments Incorporated



SNVS552B - MARCH 2008 - REVISED APRIL 2013

www.ti.com

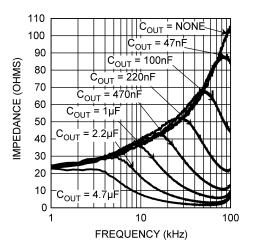


Figure 23. Reverse Dynamic Impedance vs C<sub>OUT</sub>

As with other regulators, an external capacitor reduces the amplitude of the  $V_{REF}$  transient when a sudden change in loading takes place. The capacitor should be placed as close to the part as possible to reduce the effects of unwanted board parasitics.

#### THERMAL HYSTERESIS

Thermal hysteresis is the defined as the change in output voltage at 25°C after some deviation from 25°C. This is to say that thermal hysteresis is the difference in output voltage between two points in a given temperature profile. An illustrative temperature profile is shown in Figure 24.

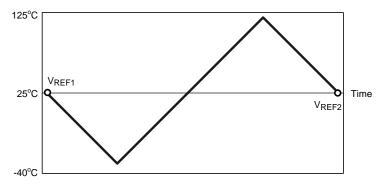


Figure 24. Illustrative Temperature Profile

This may be expressed analytically as the following:

$$V_{HYS} = \frac{IV_{REF1} - V_{REF2}I}{V_{REF}} \times 10^{6} \text{ ppm}$$

where

- V<sub>HYS</sub> = Thermal hysteresis expressed in ppm
- V<sub>REF</sub> = Nominal preset output voltage
- $V_{REF1} = V_{REF}$  before temperature fluctuation
- V<sub>REF2</sub> = V<sub>REF</sub> after temperature fluctuation

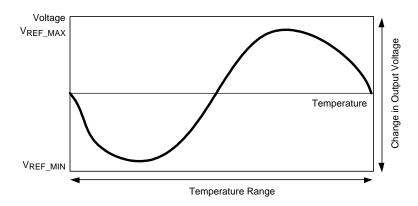
The LM4030 features a low thermal hysteresis of 75 ppm (typical) from -40°C to 125°C after 8 temperature cycles.

(2)



### TEMPERATURE COEFFICIENT

Temperature drift is defined as the maximum deviation in output voltage over the temperature range. This deviation over temperature may be illustrated as shown in Figure 25.



#### Figure 25. Illustrative V<sub>REF</sub> vs Temperature Profile

Temperature coefficient may be expressed analytically as the following:

$$T_{\rm D} = \frac{(V_{\rm REF}MAX} - V_{\rm REF}MIN)}{V_{\rm REF} \times \Delta T} \times 10^6 \, \text{ppm}$$

where

- $T_D$  = Temperature drift
- V<sub>REF</sub> = Nominal preset output voltage
- V<sub>REF MIN</sub> = Minimum output voltage over operating temperature range
- V<sub>REF MAX</sub> = Maximum output voltage over operating temperature range
- ΔT = Operating temperature range

The LM4030 features a low temperature drift of 10ppm (max) to 30ppm (max), depending on the grade.

### DYNAMIC OFFSET CANCELLATION AND LONG TERM STABILITY

Aside from initial accuracy and drift performance, other specifications such as thermal hysteresis and long-term stability can affect the accuracy of a voltage reference, especially over the lifetime of the application. The reference voltage can also shift due to board stress once the part is mounted onto the PCB and during subsequent thermal cycles. Generally, these shifts in VREF arise due to offsets between matched devices within the regulation loop. Both passive and active devices naturally experience drift over time and stress and temperature gradients across the silicon die also generate offset. The LM4030 incorporates a dynamic offset cancellation scheme which compensates for offsets developing within the regulation loop. This gives the LM4030 excellent long-term stability (40 ppm typical) and thermal hysteresis performance (75ppm typical), as well as substantial immunity to PCB stress effects, despite being packaged in a tiny SOT-23.

#### EXPRESSION OF ELECTRICAL CHARACTERISTICS

Electrical characteristics are typically expressed in mV, ppm, or a percentage of the nominal value. Depending on the application, one expression may be more useful than the other. To convert one quantity to the other one may apply the following:

ppm to mV error in output voltage:

$$\frac{V_{REF} x ppm_{ERROR}}{10^3} = V_{ERROR}$$

where

 $V_{REF}$  is in volts (V) and  $V_{ERROR}$  is in milli-volts (mV)

(3)

SNVS552B-MARCH 2008-REVISED APRIL 2013



www.ti.com

(6)

(7)

Bit error (1 bit) to voltage error (mV):

$$\frac{V_{\text{REF}}}{2^n} \times 10^3 = V_{\text{ERROR}}$$
(5)

V<sub>REF</sub> is in volts (V), V<sub>ERROR</sub> is in milli-volts (mV), and n is the number of bits.

mV to ppm error in output voltage:

 $\frac{V_{ERROR}}{V_{REF}} \times 10^3 = ppm_{ERROR}$ 

where

•  $V_{REF}$  is in volts (V) and  $V_{ERROR}$  is in milli-volts (mV)

Voltage error (mV) to percentage error (percent):

 $\frac{V_{ERROR}}{V_{REF}} \times 0.1 = Percent\_Error$ 

where

-  $V_{REF}$  is in volts (V) and  $V_{ERROR}$  is in milli-volts (mV)

## PRINTED CIRCUIT BOARD and LAYOUT CONSIDERATIONS

The LM4030 has a very small change in reverse voltage with current (25ppm/mA typical) so large variations in load current (up to 50mA) should not appreciably shift VREF. Parasitic resistance between the LM4030 and the load introduces a voltage drop proportional to load current and should be minimized. The LM4030 should be placed as close to the load it is driving as the layout will allow. The location of  $R_z$  is not important, but  $C_{OUT}$  should be as close to the LM4030 as possible so added ESR does not degrade the transient performance.

SNVS552B - MARCH 2008 - REVISED APRIL 2013

Changes from Revision A (April 2013) to Revision B						
•	Changed layout of National Data Sheet to TI format	. 12				



23-Aug-2017

## PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LM4030AMF-2.5/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5JA	Samples
LM4030AMF-4.096/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5KA	Samples
LM4030AMFX-2.5/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5JA	Samples
LM4030BMF-2.5/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5JB	Samples
LM4030BMF-4.096/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5KB	Samples
LM4030BMFX-2.5/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5JB	Samples
LM4030BMFX4.096/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5KB	Samples
LM4030CMF-2.5/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5JC	Samples
LM4030CMF-4.096/NOPB	ACTIVE	SOT-23	DBV	5	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5KC	Samples
LM4030CMFX-2.5/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5JC	Samples
LM4030CMFX4.096/NOPB	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	R5KC	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.



23-Aug-2017

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

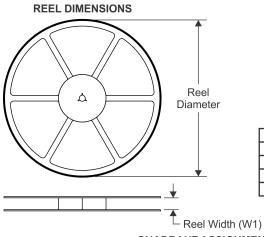
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

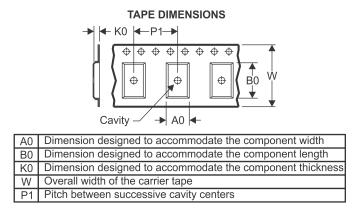
# PACKAGE MATERIALS INFORMATION

www.ti.com

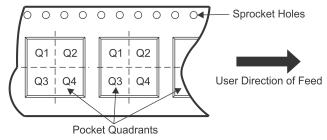
Texas Instruments

### TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



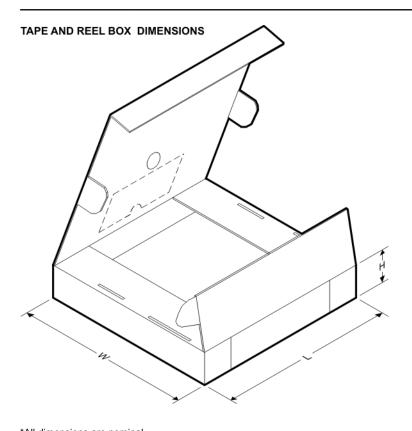
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM4030AMF-2.5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030AMF-4.096/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030AMFX-2.5/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030BMF-2.5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030BMF-4.096/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030BMFX-2.5/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030BMFX4.096/NOP B	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030CMF-2.5/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030CMF-4.096/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030CMFX-2.5/NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LM4030CMFX4.096/NOP B	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TEXAS INSTRUMENTS

www.ti.com

## PACKAGE MATERIALS INFORMATION

24-Aug-2017

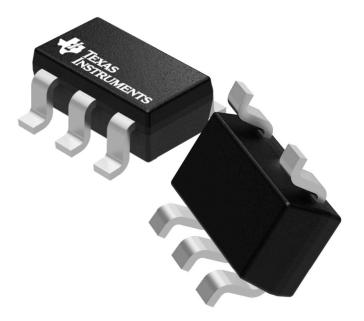


*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM4030AMF-2.5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM4030AMF-4.096/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM4030AMFX-2.5/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LM4030BMF-2.5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM4030BMF-4.096/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM4030BMFX-2.5/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LM4030BMFX4.096/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LM4030CMF-2.5/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM4030CMF-4.096/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
LM4030CMFX-2.5/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
LM4030CMFX4.096/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0

## DBV 5

# **GENERIC PACKAGE VIEW**

# SOT-23 - 1.45 mm max height SMALL OUTLINE TRANSISTOR



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



# **DBV0005A**



# **PACKAGE OUTLINE**

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  This drawing is subject to change without notice.
  Reference JEDEC MO-178.

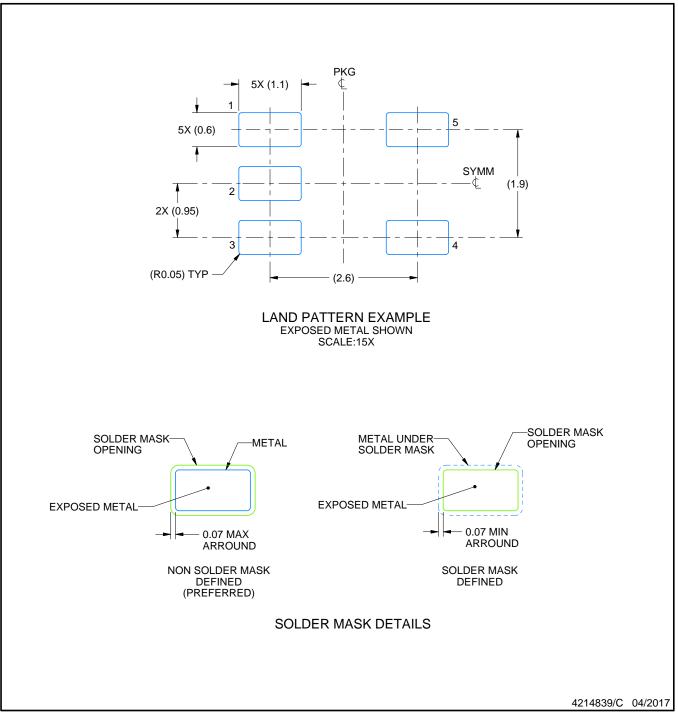


# DBV0005A

# **EXAMPLE BOARD LAYOUT**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.

5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DBV0005A

# **EXAMPLE STENCIL DESIGN**

## SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

7. Board assembly site may have different recommendations for stencil design.



<sup>6.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

#### **IMPORTANT NOTICE**

Texas Instruments Incorporated (TI) reserves the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete.

TI's published terms of sale for semiconductor products (http://www.ti.com/sc/docs/stdterms.htm) apply to the sale of packaged integrated circuit products that TI has qualified and released to market. Additional terms may apply to the use or sale of other types of TI products and services.

Reproduction of significant portions of TI information in TI data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such reproduced documentation. Information of third parties may be subject to additional restrictions. Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyers and others who are developing systems that incorporate TI products (collectively, "Designers") understand and agree that Designers remain responsible for using their independent analysis, evaluation and judgment in designing their applications and that Designers have full and exclusive responsibility to assure the safety of Designers' applications and compliance of their applications (and of all TI products used in or for Designers' applications) with all applicable regulations, laws and other applicable requirements. Designer represents that, with respect to their applications, Designer has all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. Designer agrees that prior to using or distributing any applications that include TI products, Designer will thoroughly test such applications and the functionality of such TI products as used in such applications.

TI's provision of technical, application or other design advice, quality characterization, reliability data or other services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using TI Resources in any way, Designer (individually or, if Designer is acting on behalf of a company, Designer's company) agrees to use any particular TI Resource solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

Designer is authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS. TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY DESIGNER AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

Unless TI has explicitly designated an individual product as meeting the requirements of a particular industry standard (e.g., ISO/TS 16949 and ISO 26262), TI is not responsible for any failure to meet such industry standard requirements.

Where TI specifically promotes products as facilitating functional safety or as compliant with industry functional safety standards, such products are intended to help enable customers to design and create their own applications that meet applicable functional safety standards and requirements. Using products in an application does not by itself establish any safety features in the application. Designers must ensure compliance with safety-related requirements and standards applicable to their applications. Designer may not use any TI products in life-critical medical equipment unless authorized officers of the parties have executed a special contract specifically governing such use. Life-critical medical equipment is medical equipment where failure of such equipment would cause serious bodily injury or death (e.g., life support, pacemakers, defibrillators, heart pumps, neurostimulators, and implantables). Such equipment includes, without limitation, all medical devices identified by the U.S. Food and Drug Administration as Class III devices and equivalent classifications outside the U.S.

TI may expressly designate certain products as completing a particular qualification (e.g., Q100, Military Grade, or Enhanced Product). Designers agree that it has the necessary expertise to select the product with the appropriate qualification designation for their applications and that proper product selection is at Designers' own risk. Designers are solely responsible for compliance with all legal and regulatory requirements in connection with such selection.

Designer will fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of Designer's noncompliance with the terms and provisions of this Notice.

> Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2018, Texas Instruments Incorporated